

2N3419
2N3420
2N3421

**SILICON
NPN TRANSISTORS**



TO-39 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3419, 2N3420, and 2N3421 are silicon NPN transistors manufactured by the epitaxial planar process, and designed for small signal general purpose and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N3420	2N3419 2N3421	UNITS
Collector-Base Voltage	V_{CBO}	85	125	V
Collector-Emitter Voltage	V_{CEO}	60	80	V
Emitter-Base Voltage	V_{EBO}		8.0	V
Continuous Collector Current	I_C		3.0	A
Peak Collector Current ($PW \leq 1.0\text{ms}$, D.C. $\leq 50\%$)	I_{CM}		5.0	A
Continuous Base Current	I_B		1.0	A
Power Dissipation	P_D		1.0	W
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D		15	W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3420		2N3419 2N3421		UNITS
		MIN	MAX	MIN	MAX	
I_{CEX}	$V_{CE}=80\text{V}, V_{EB}=0.5\text{V}$	-	500	-	-	nA
I_{CEX}	$V_{CE}=120\text{V}, V_{EB}=0.5\text{V}$	-	-	-	500	nA
I_{CEX}	$V_{CE}=80\text{V}, V_{EB}=0.5\text{V}, T_C=150^\circ\text{C}$	-	50	-	-	μA
I_{CEX}	$V_{CE}=120\text{V}, V_{EB}=0.5\text{V}, T_C=150^\circ\text{C}$	-	-	-	50	μA
I_{EBO}	$V_{EB}=6.0\text{V}$	-	500	-	500	nA
I_{EBO}	$V_{EB}=8.0\text{V}$	-	10	-	10	μA
BV_{CEO}	$I_C=50\text{mA}$	60	-	80	-	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	-	0.25	-	0.25	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$	-	0.50	-	0.50	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	0.6	1.2	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$	0.7	1.4	0.7	1.4	V
f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=20\text{MHz}$	40	-	40	-	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$	-	150	-	150	pF
t_{on}	$V_{EB(OFF)}=3.7\text{V}, I_C=1.0\text{A},$	-	300	-	300	ns
t_{off}	$I_{B1}=I_{B2}=100\text{mA}, R_L=20\Omega$	-	1.2	-	1.2	μs

R0 (24-March 2014)

2N3419
2N3420
2N3421

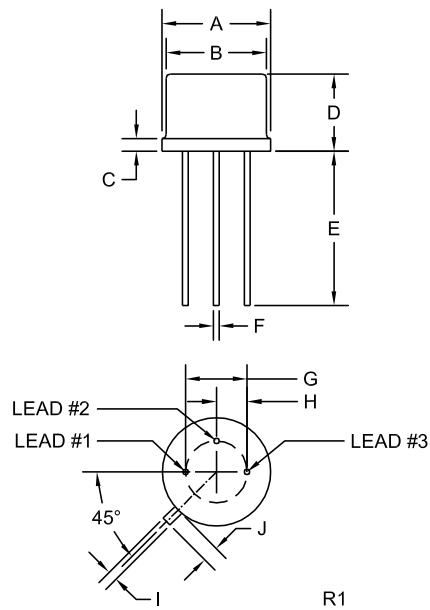
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	2N3419		2N3420 2N3421		UNITS
		MIN	MAX	MIN	MAX	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=100\text{mA}$	20	-	40	-	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$	20	60	40	160	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=2.0\text{A}$	15	-	30	-	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=5.0\text{A}$	10	-	15	-	

TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R0 (24-March 2014)